



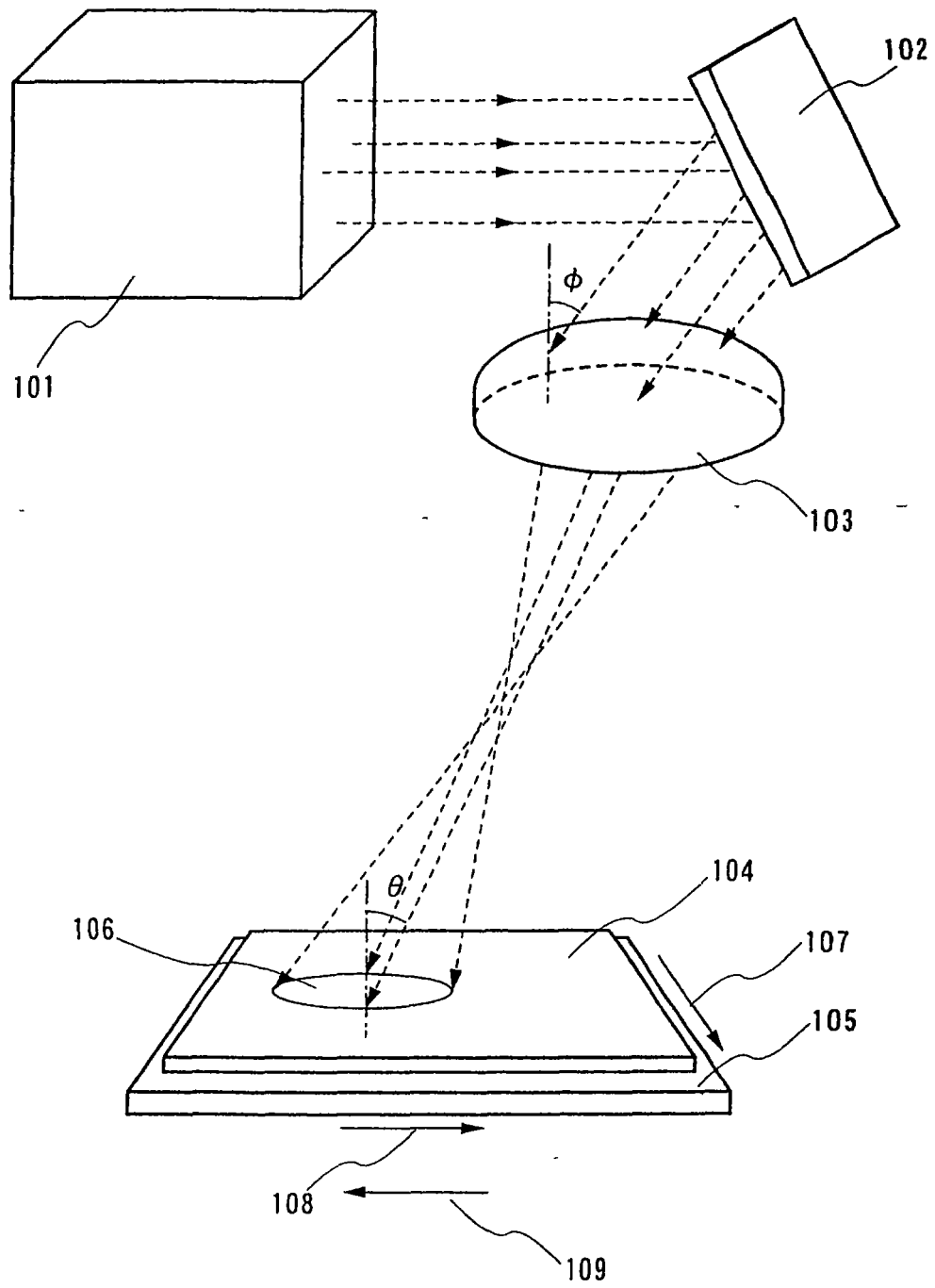
163163

1/28



G00002

Fig. 1



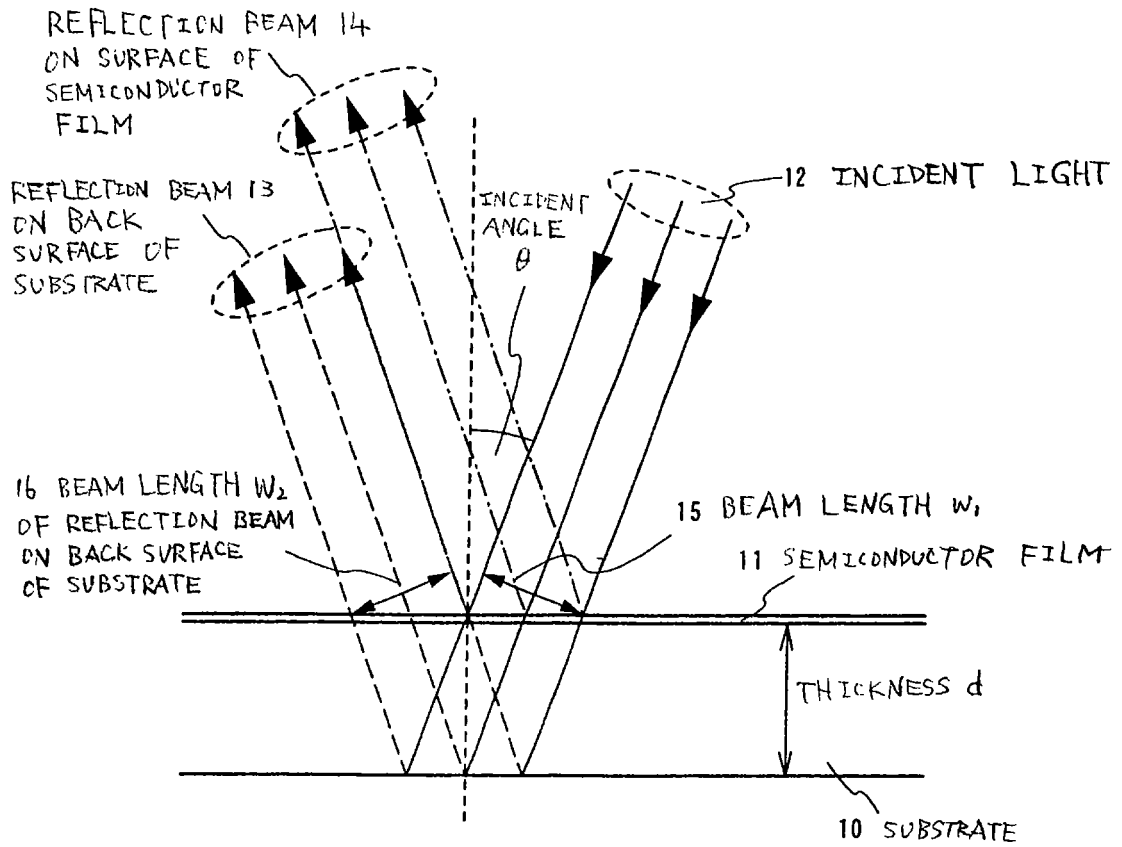


Fig.2

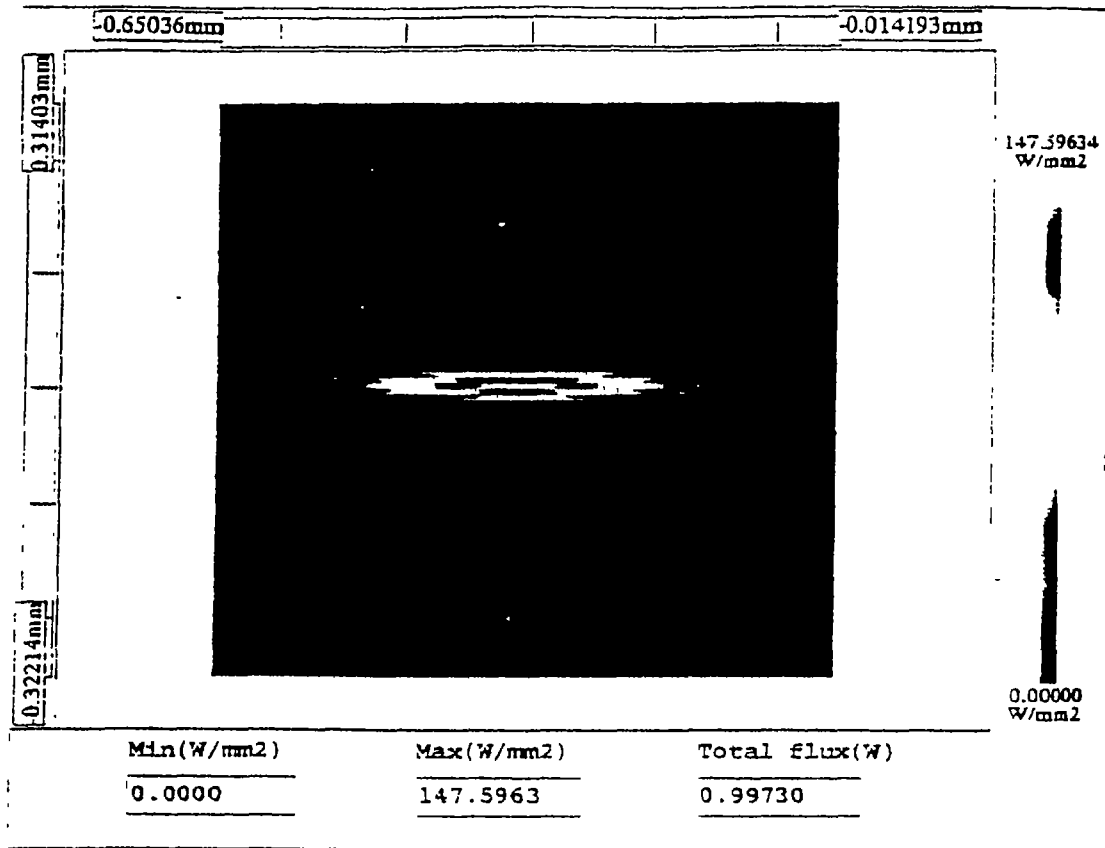
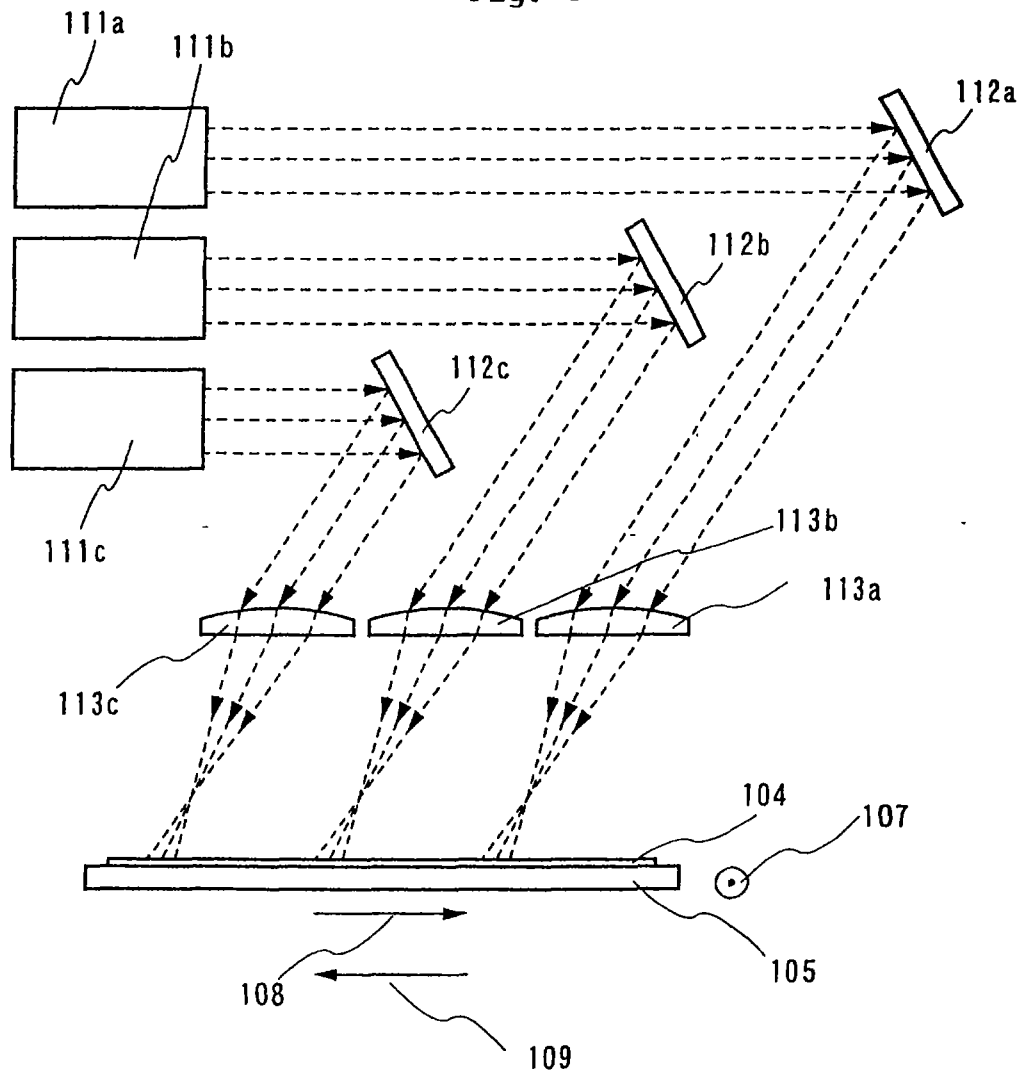


Fig.3

Fig. 4



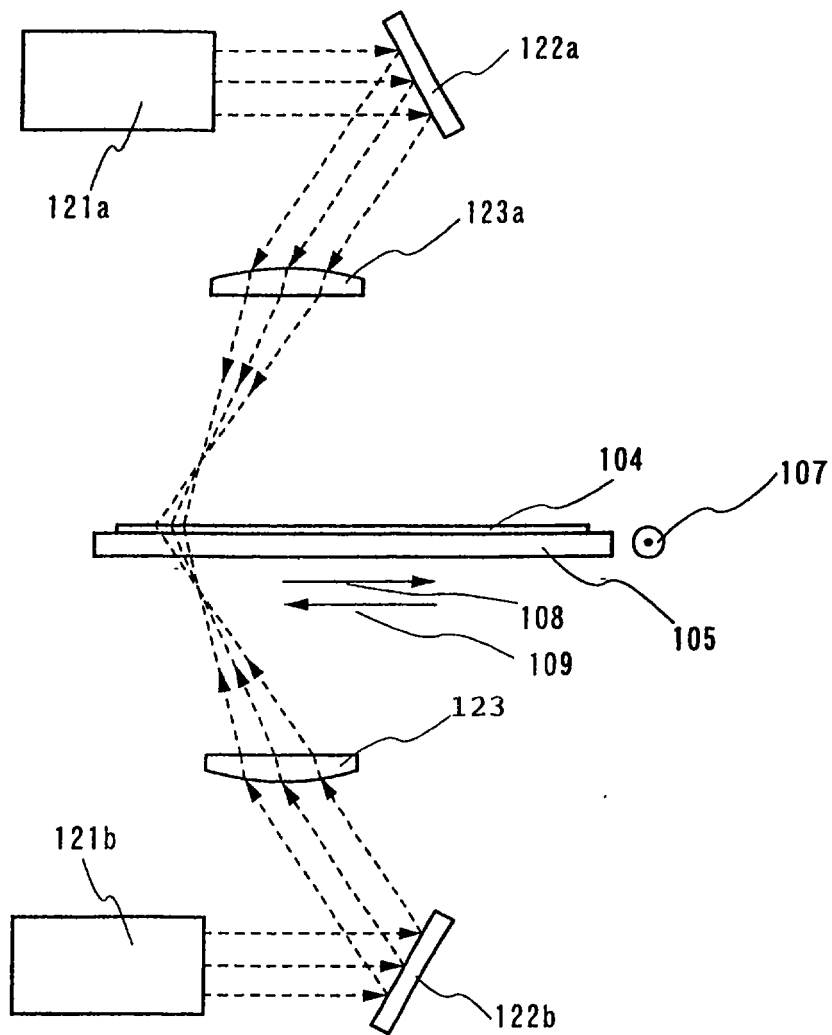


Fig. 5

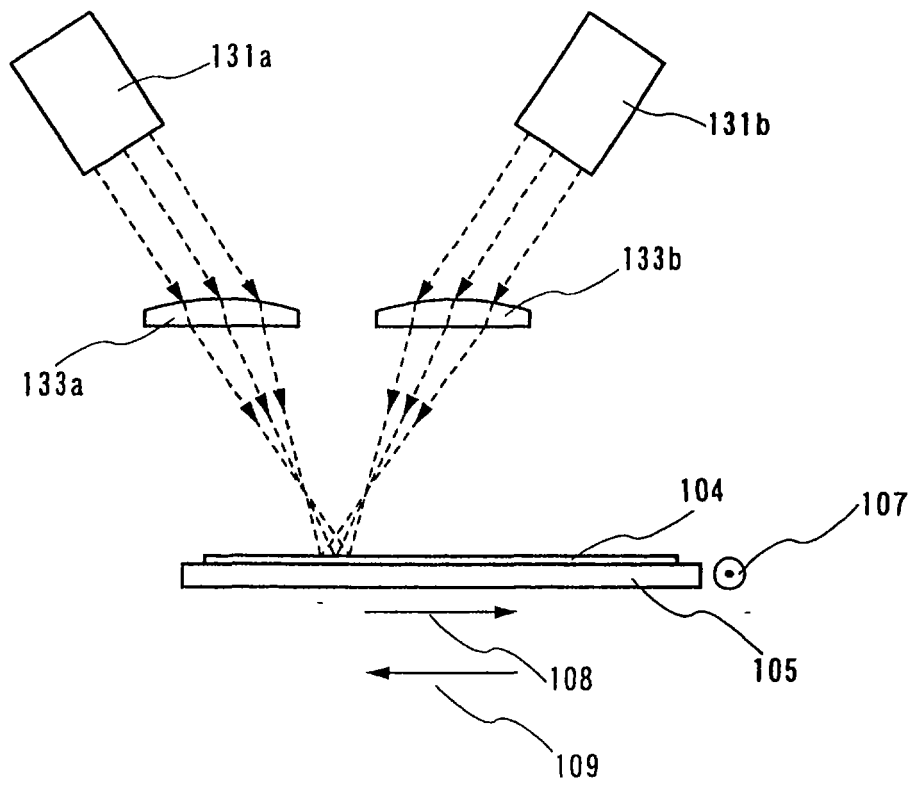
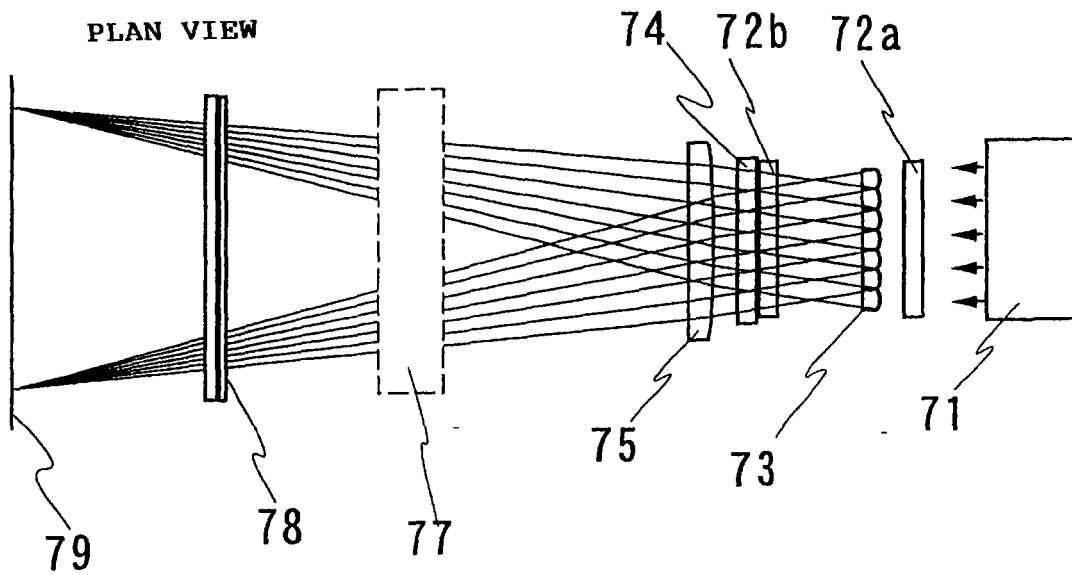


Fig. 6

Fig. 7

SIDE VIEW

77 72b 75 74 73 71 72a 79 78

The side view shows the profile of the components and the path of the light rays. The rays originate from a point (79) and pass through a component (78), then through a series of components (77, 72b, 75, 74, 73, 71, 72a). The rays are shown as multiple lines, indicating a fan beam or a series of parallel rays. The components are shown as vertical rectangles, and the rays are shown as lines connecting the points of entry and exit.

FORMATION OF BASE FILM/FORMATION OF SEMICONDUCTOR LAYER/FORMATION OF INSULATING FILM/
FORMATION OF FIRST CONDUCTIVE FILM AND SECOND CONDUCTIVE FILM

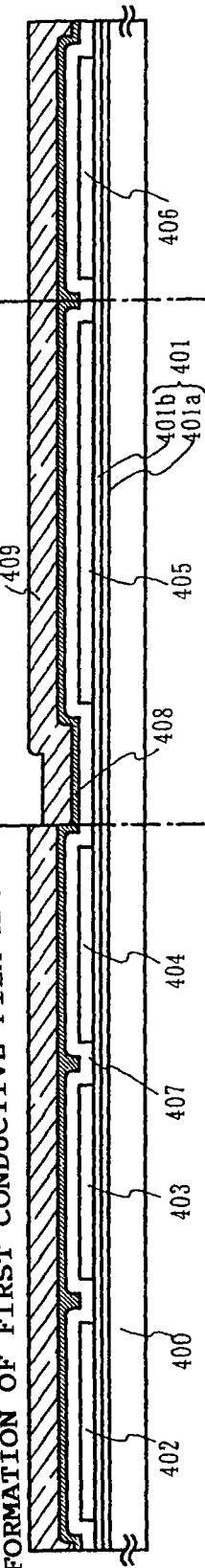
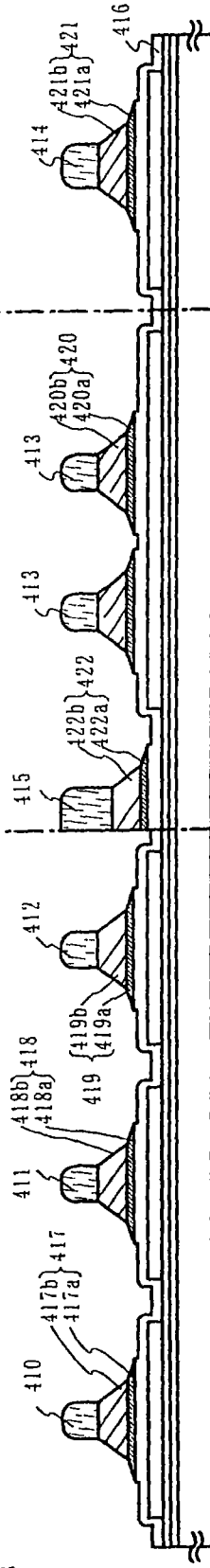


Fig. 8A

FIRST ETCHING PROCESS

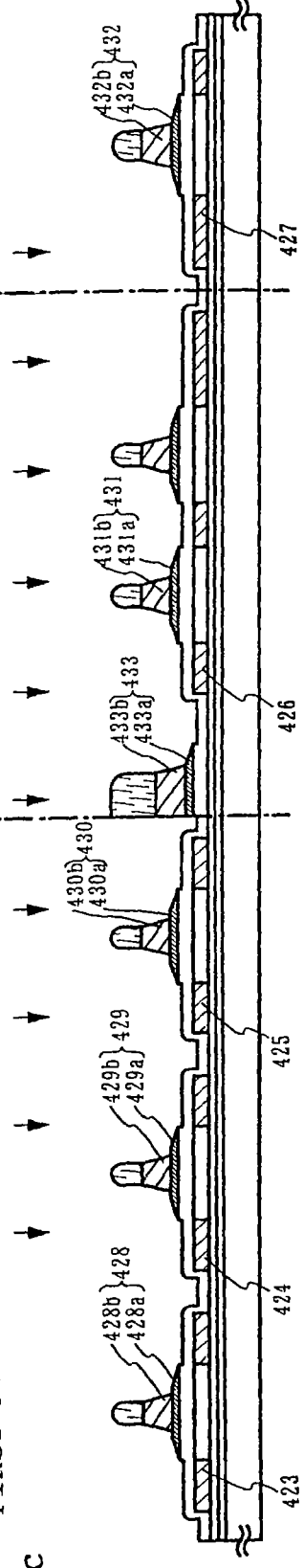
Fig. 8B



SECOND ETCHING PROCESS

FIRST DOPING PROCESS

Fig. 8C



SECOND DOPING PROCESS/THIRD DOPING PROCESS

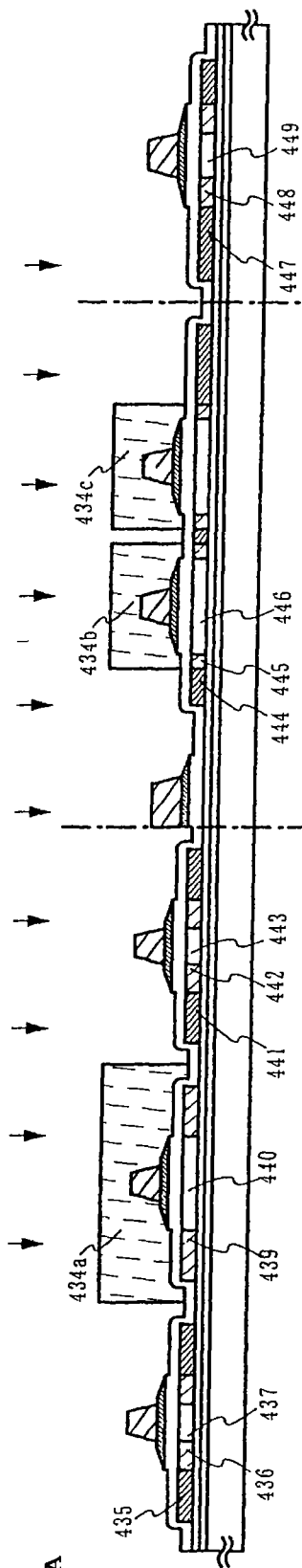


Fig. 9A

FOURTH DOPING PROCESS

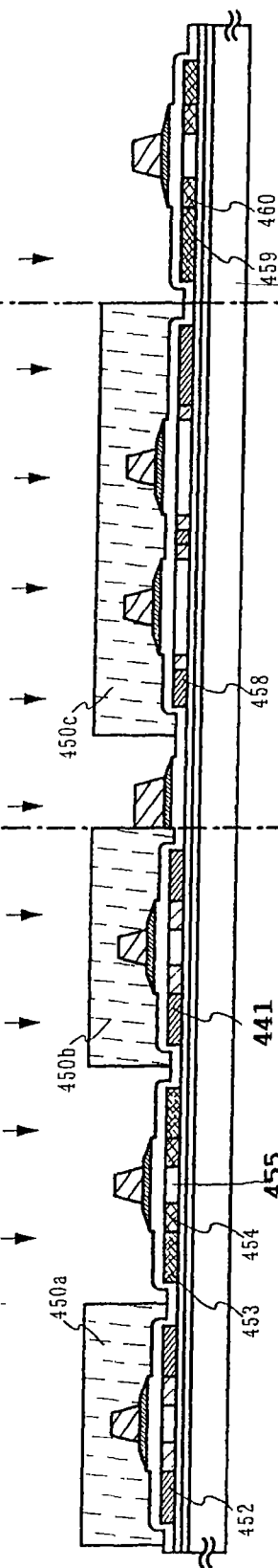


Fig. 9B

FORMATION OF FIRST INTERLAYER INSULATING FILM/LASER BEAM IRRADIATION/HEAT TREATMENT

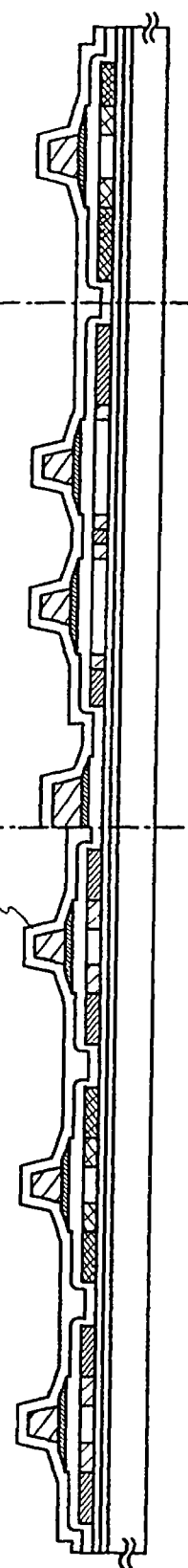


Fig. 9C

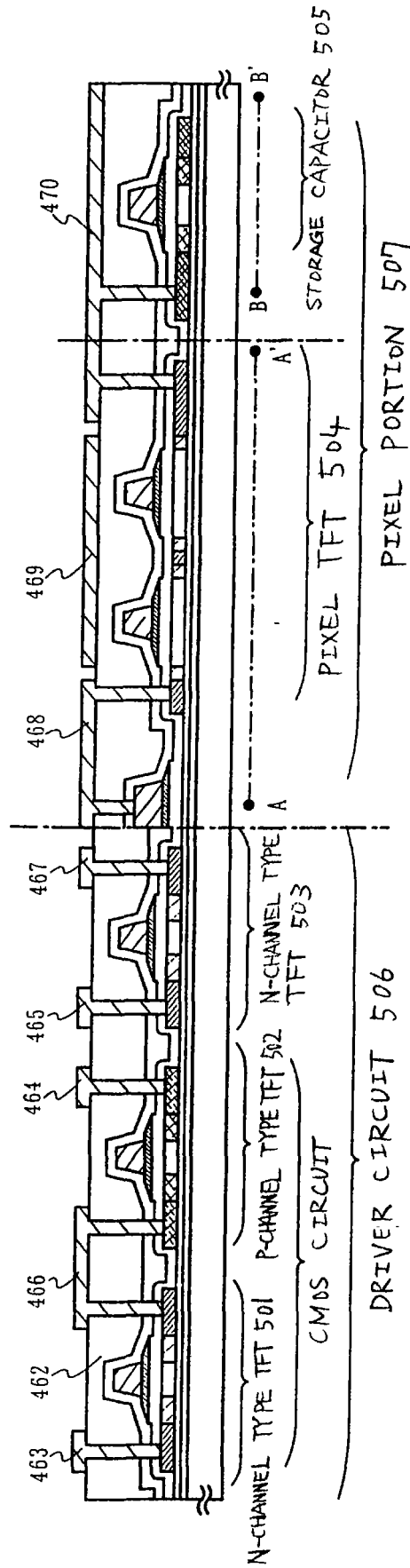
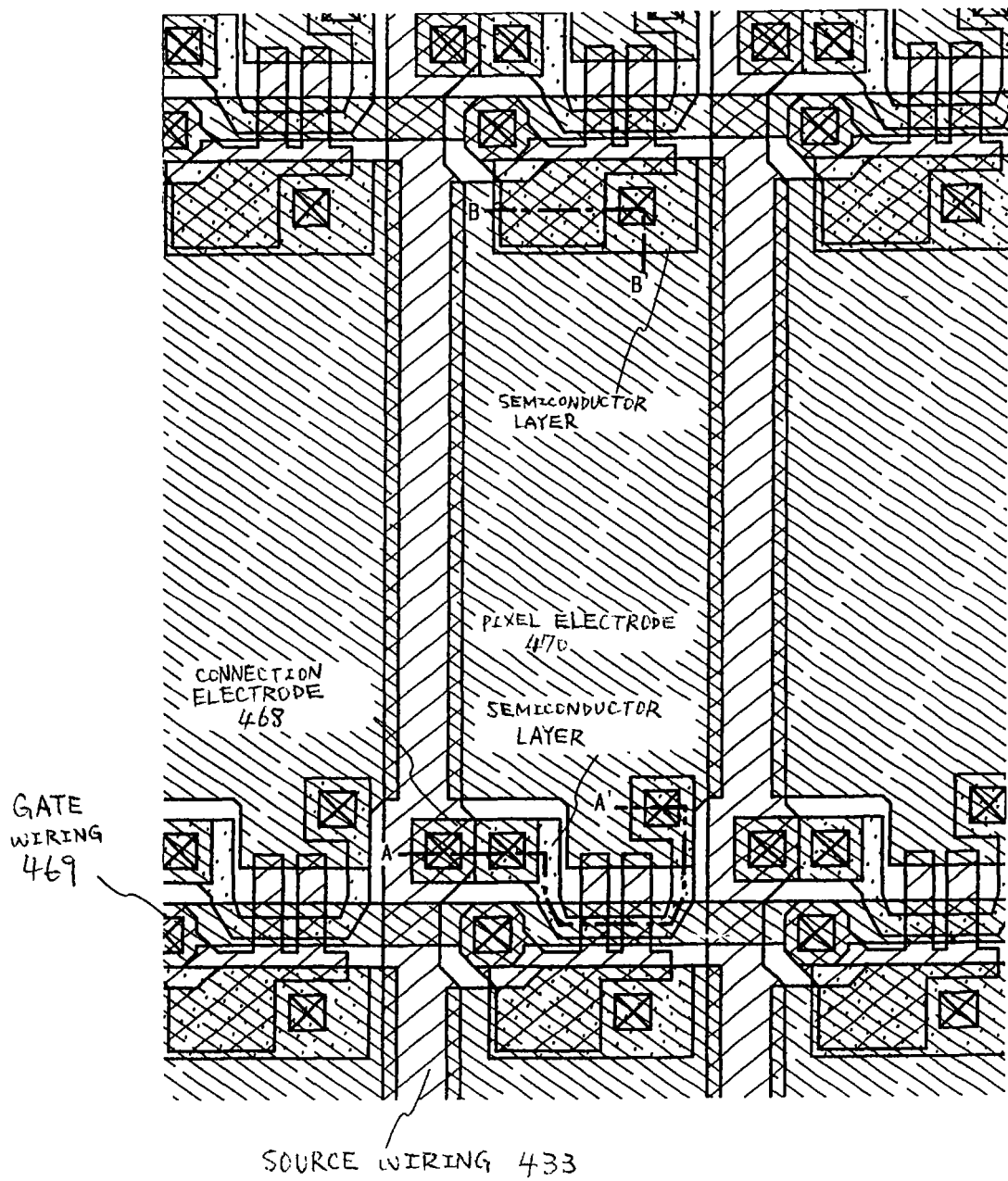


Fig. 10

Fig. 11



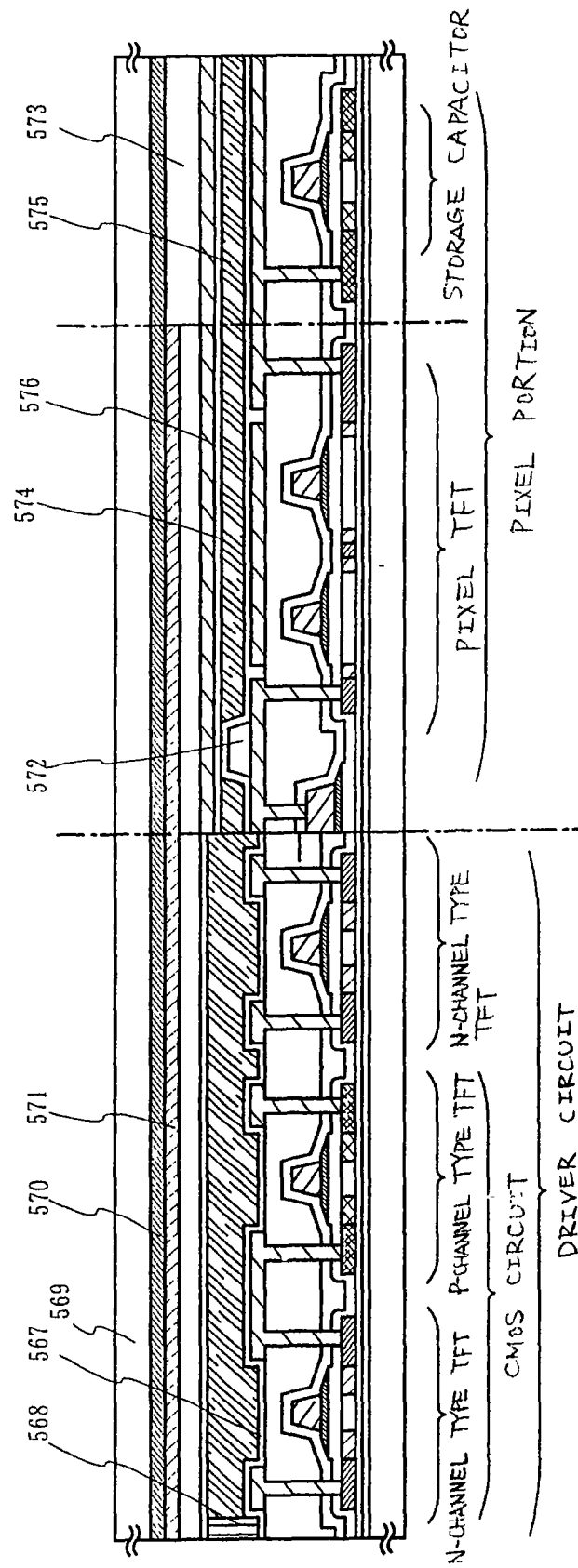


Fig. 12

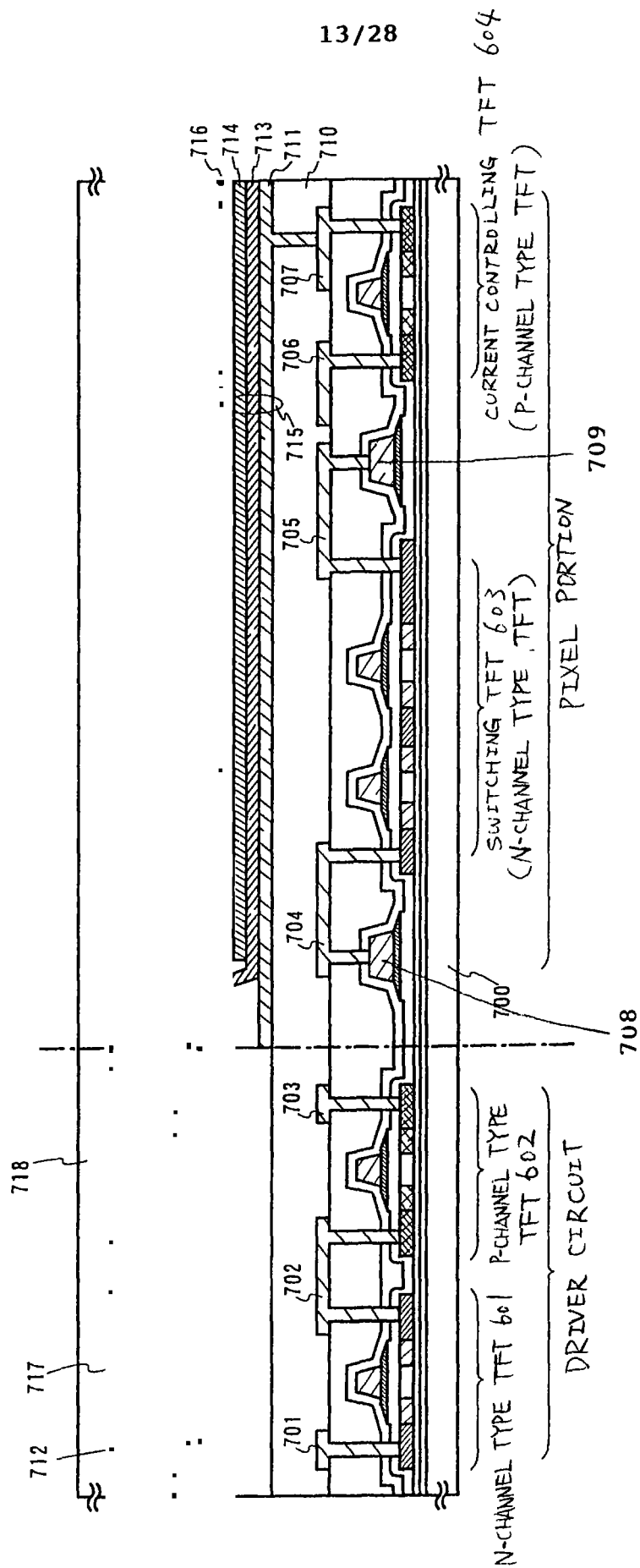
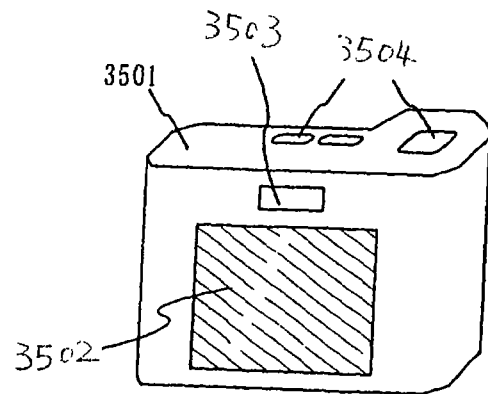
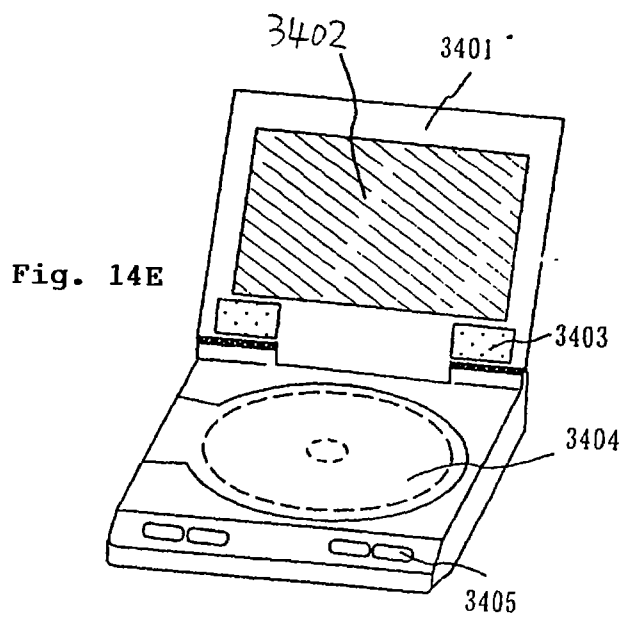
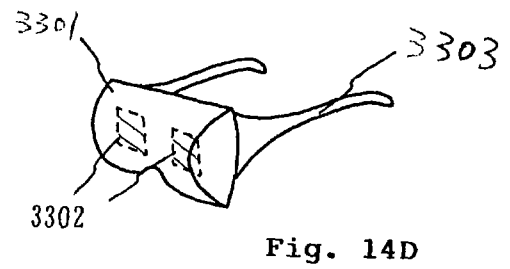
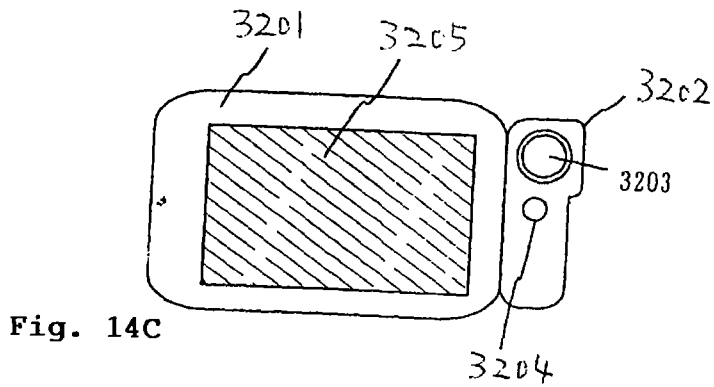
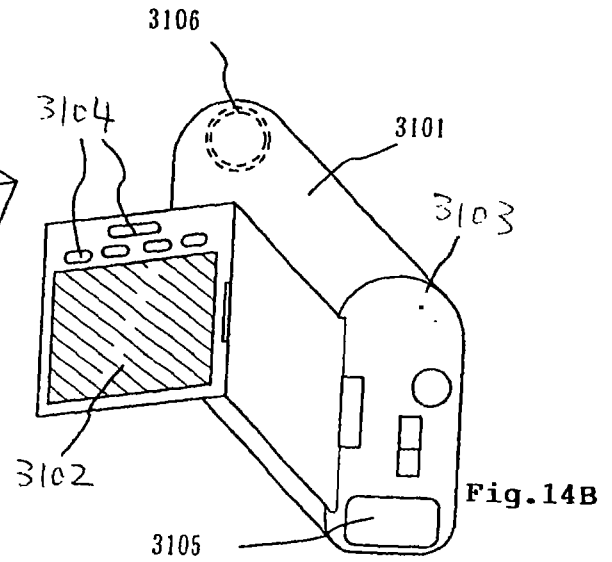
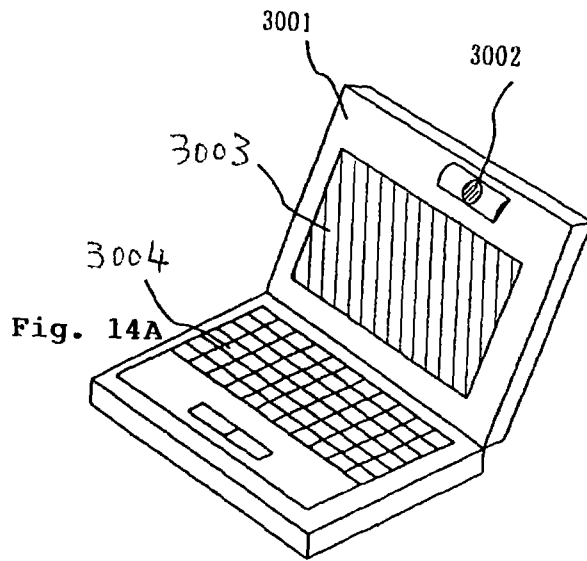
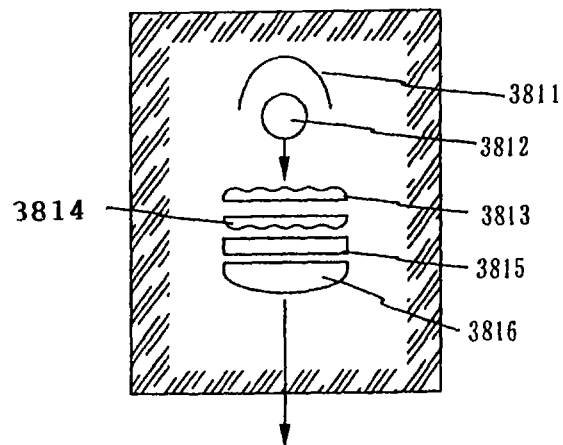
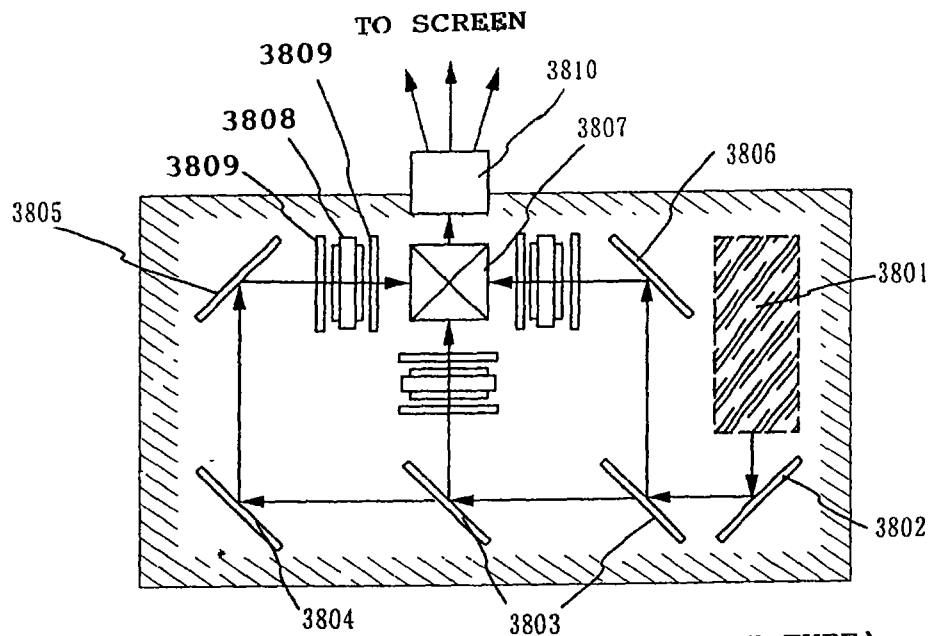
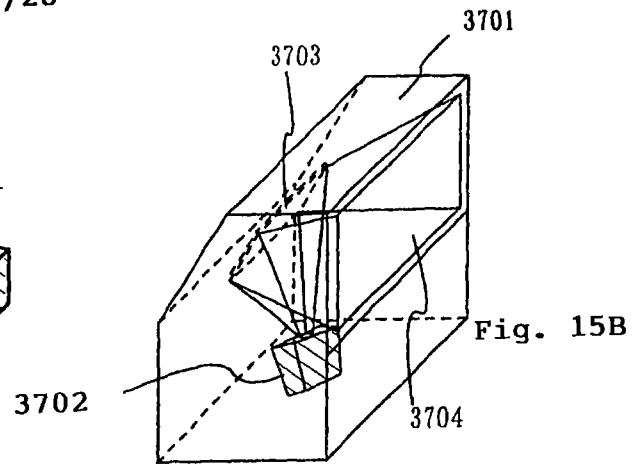
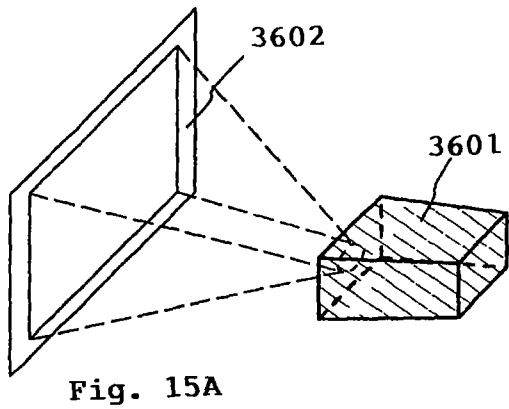
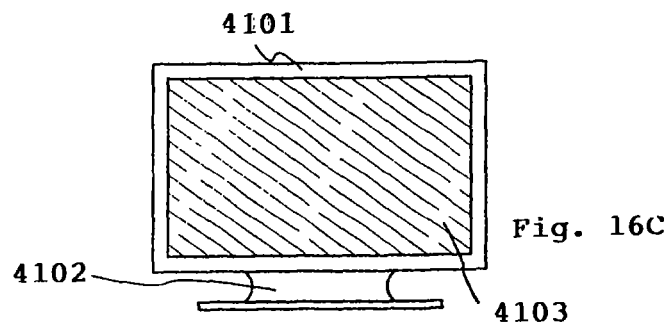
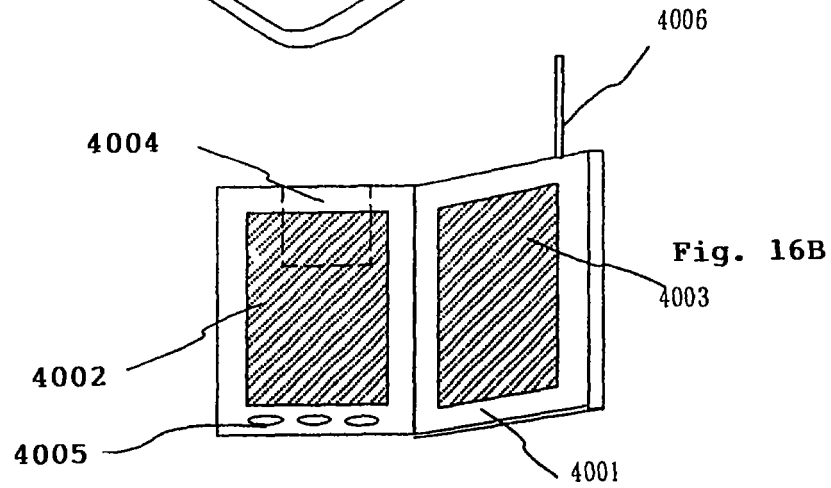
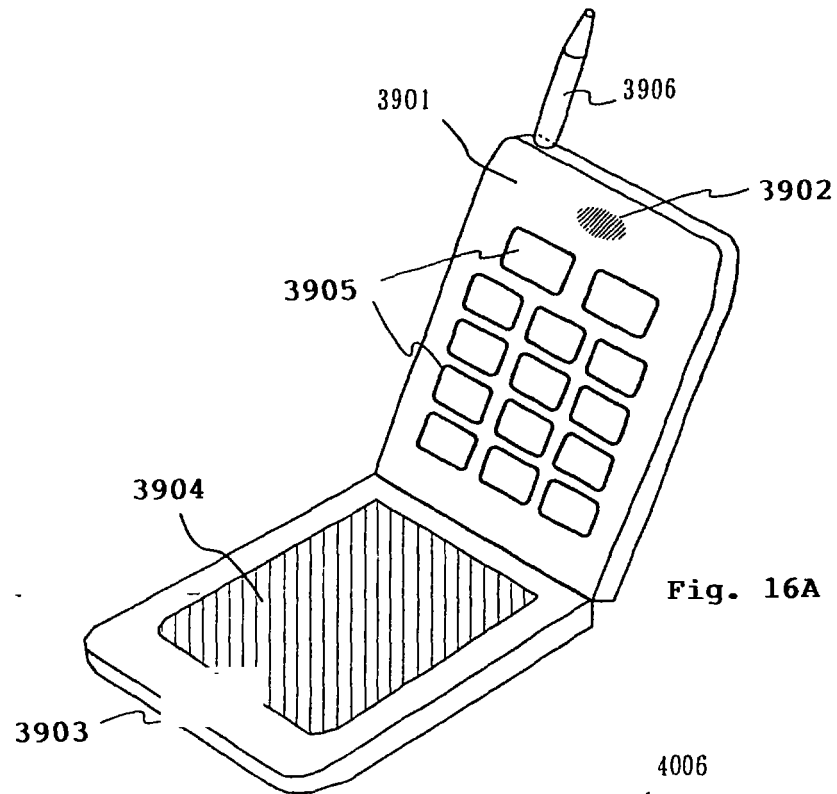


Fig. 13





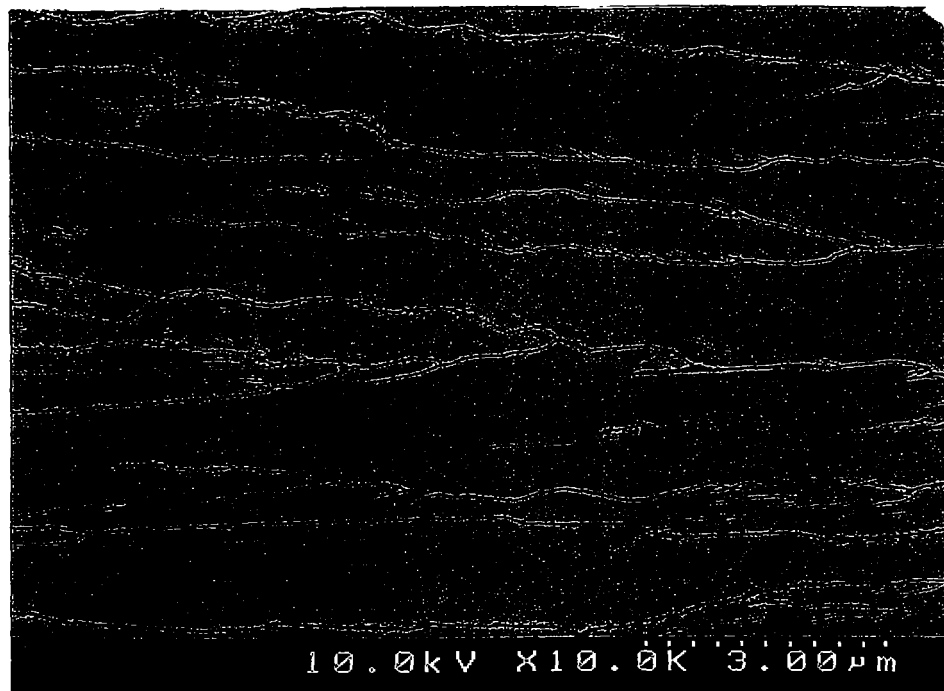
LIGHT SOURCE
OPTICAL SYSTEM





→
RELATIVE SCANNING DIRECTION OF LASER BEAM

Fig.17



→
RELATIVE SCANNING DIRECTION OF LASER BEAM

Fig.18

Fig. 19A FORMATION OF BASE INSULATING FILM /
FORMATION OF SEMICONDUCTOR FILM

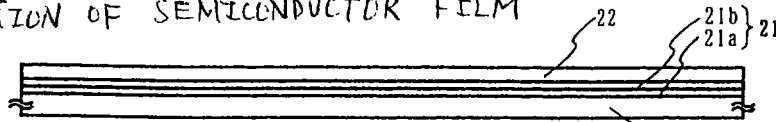


Fig. 19B CRYSTALLIZATION OF SEMICONDUCTOR FILM

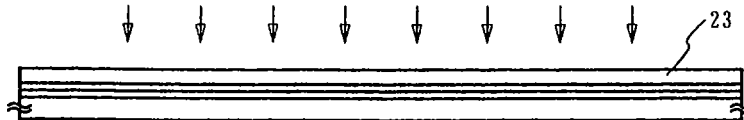


Fig. 19c FIRST DOPING PROCESS



Fig. 19D FIRST ETCHING PROCESS / FORMATION OF INSULATING FILM /
FORMATION OF CONDUCTIVE FILM

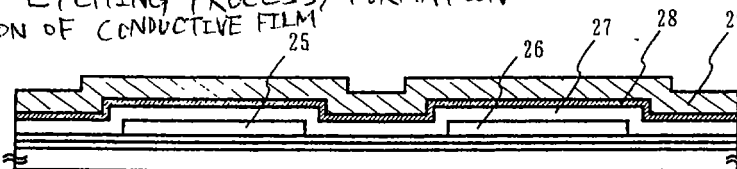


Fig. 19E SECOND ETCHING PROCESS / SECOND DOPING PROCESS

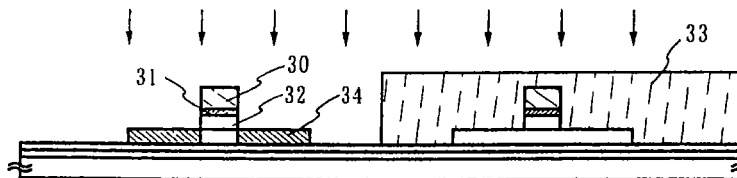


Fig. 19F THIRD DOPING PROCESS

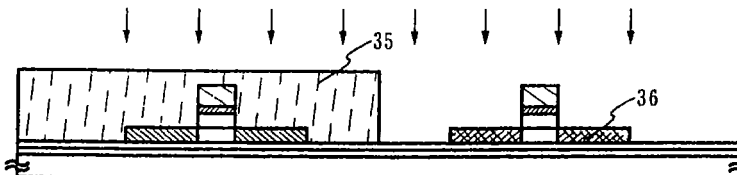


Fig. 19G FORMATION OF FIRST INTERLAYER INSULATING FILM /
HEAT TREATMENT



Fig. 19H FORMATION OF SECOND INTERLAYER INSULATING FILM /
HYDROGENATION PROCESSING / FORMATION OF WIRING

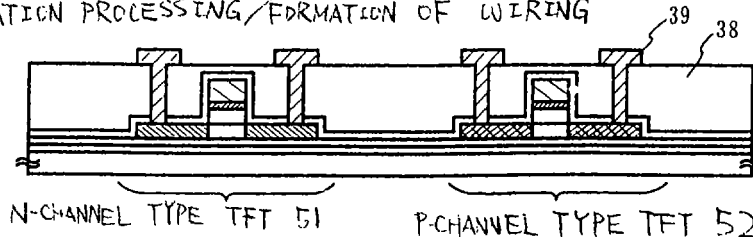


Fig. 20A

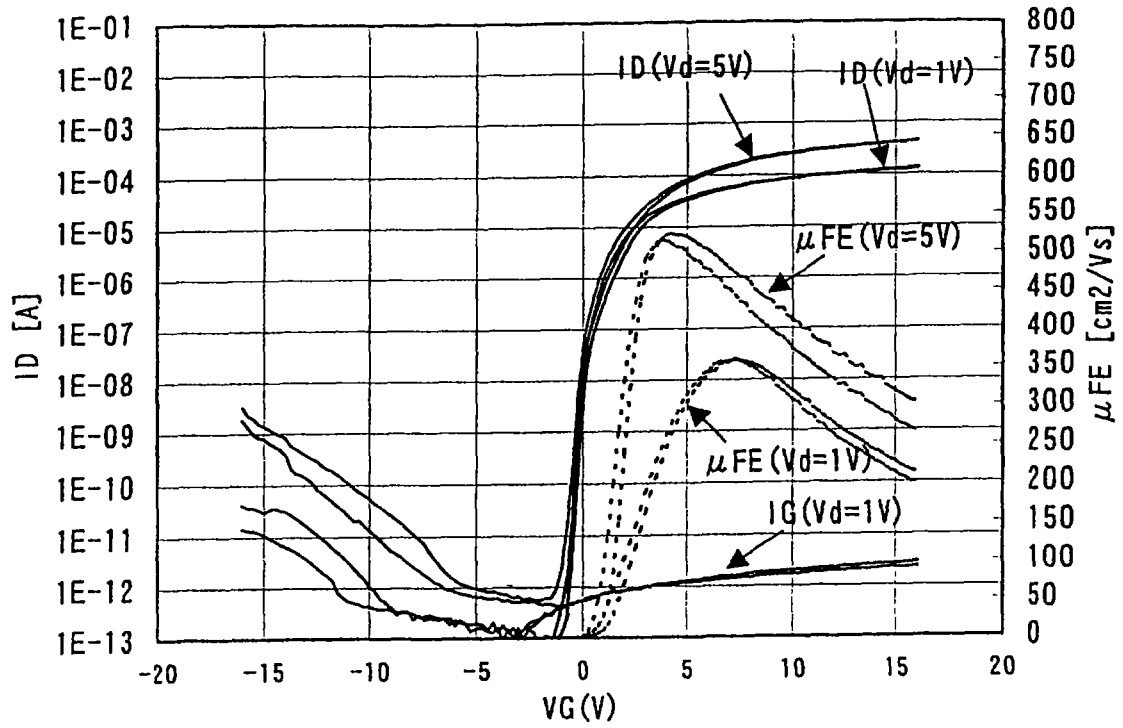
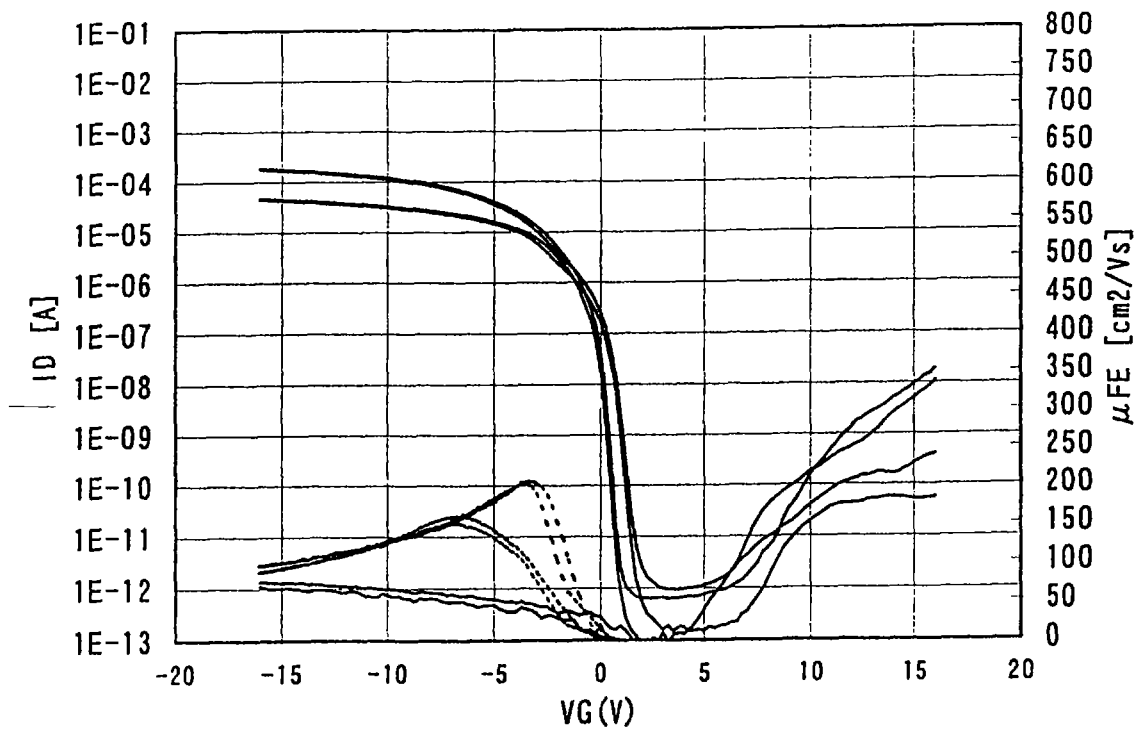


Fig. 20B



FORMATION OF METAL CONTAINING LAYER

Fig. 21A

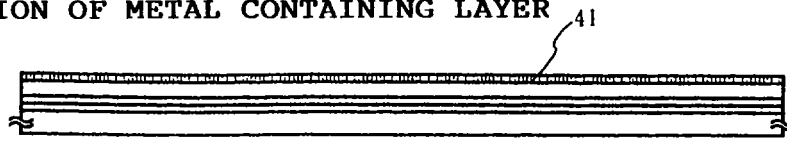


Fig. 21B

HEAT TREATMENT

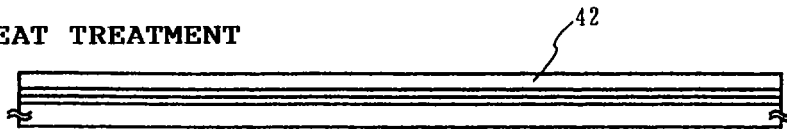


Fig. 21C

LASER ANNEALING

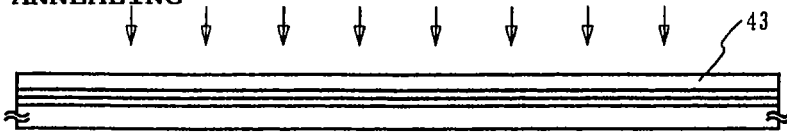


Fig. 22A

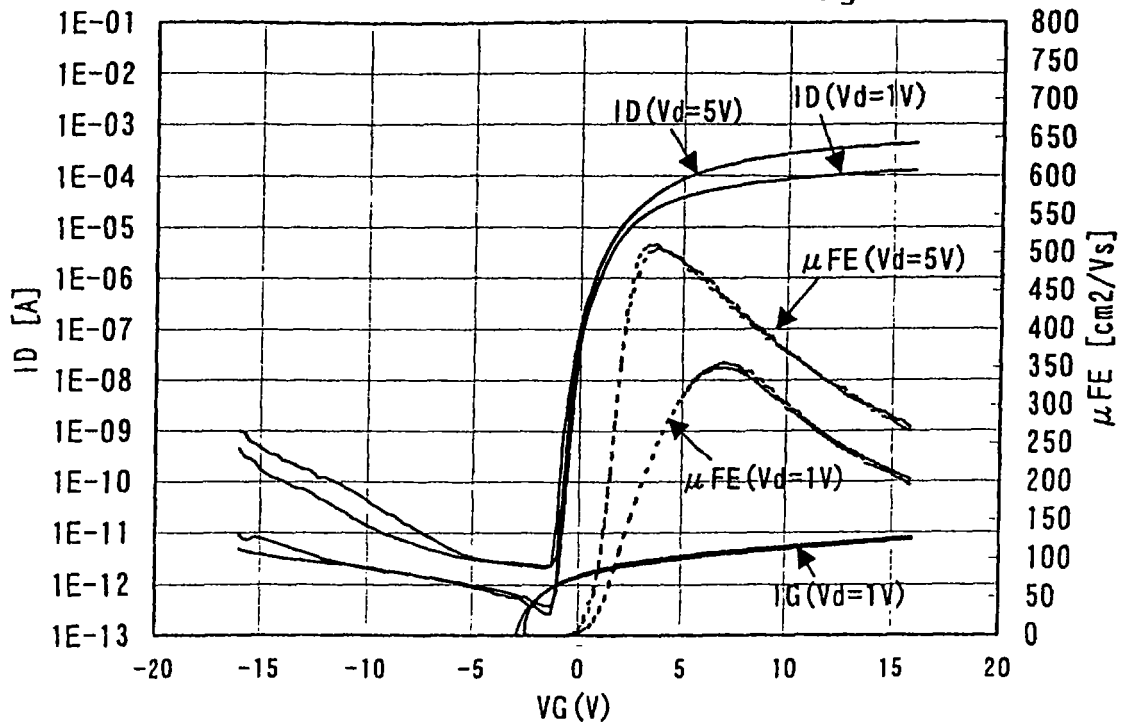


Fig. 22B

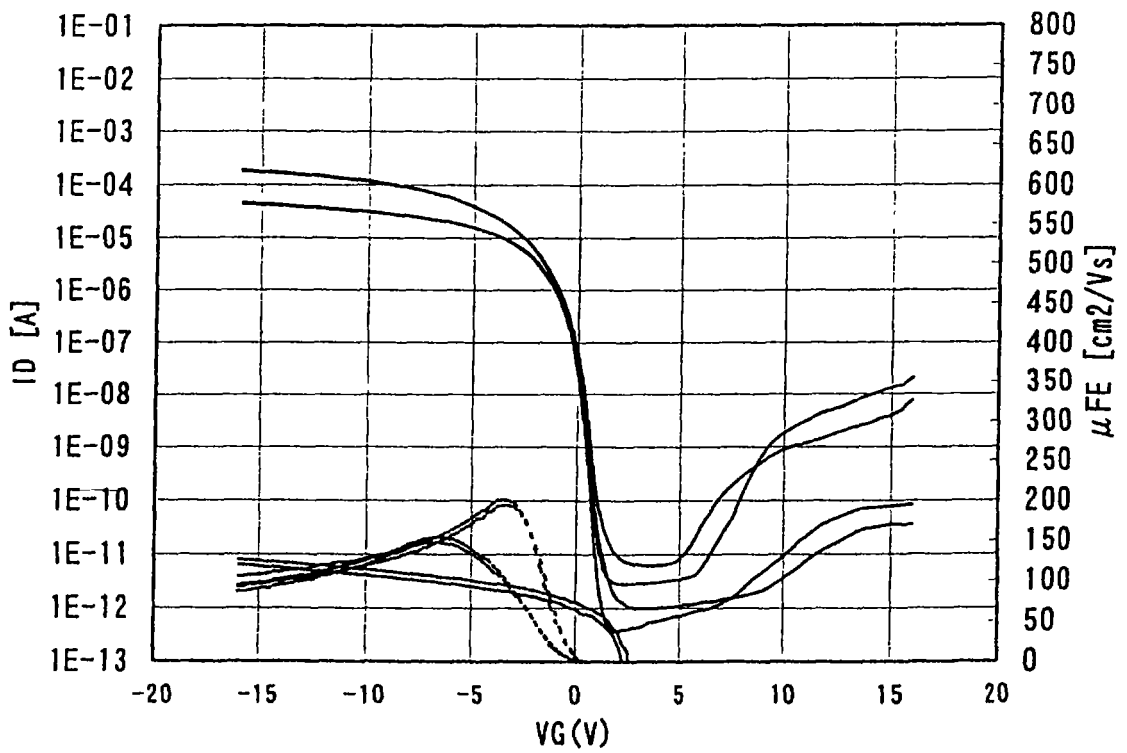


Fig. 23A

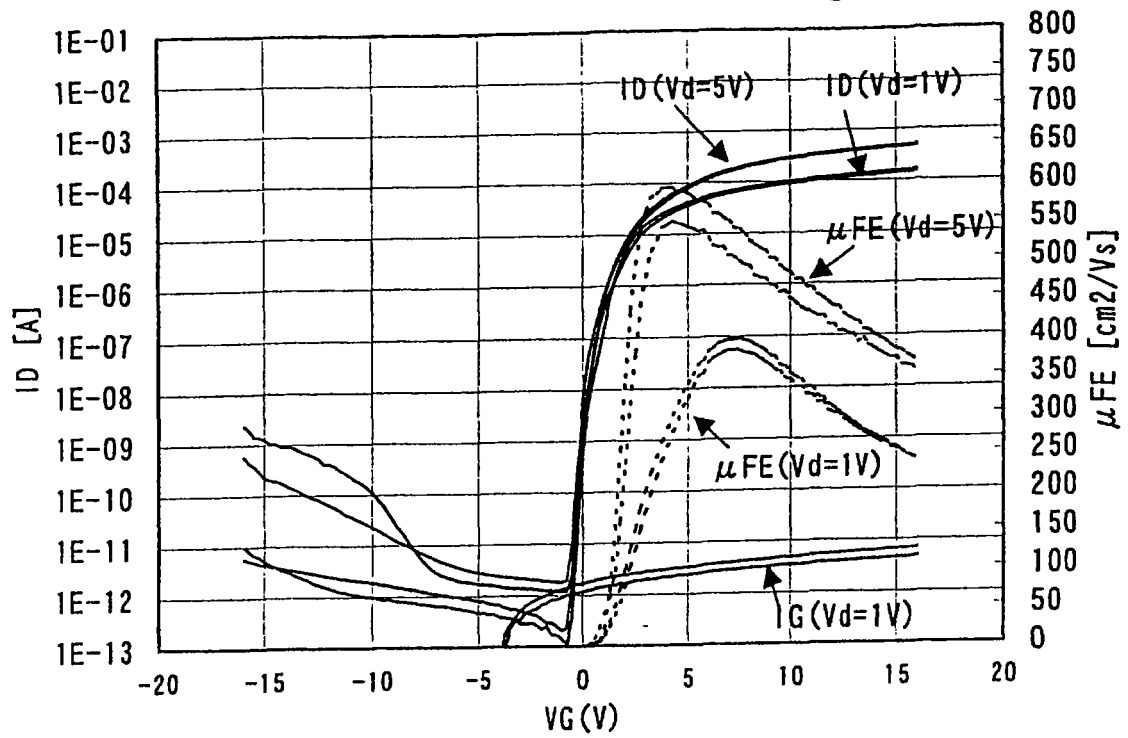
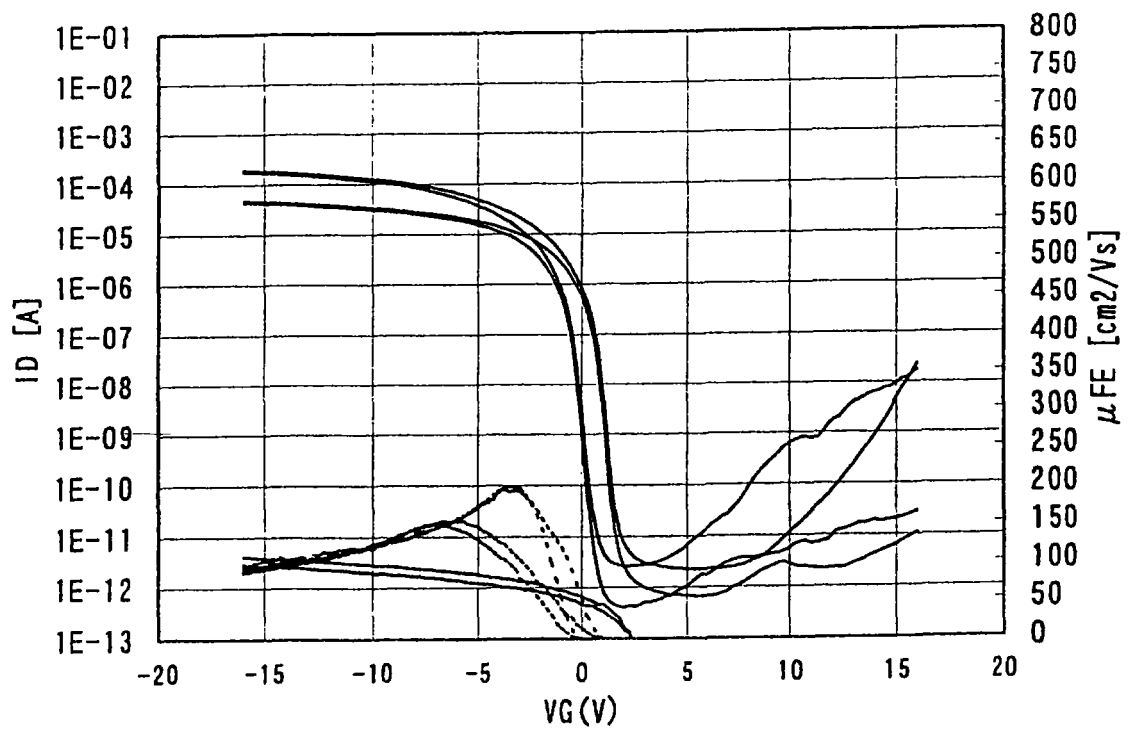


Fig. 23B



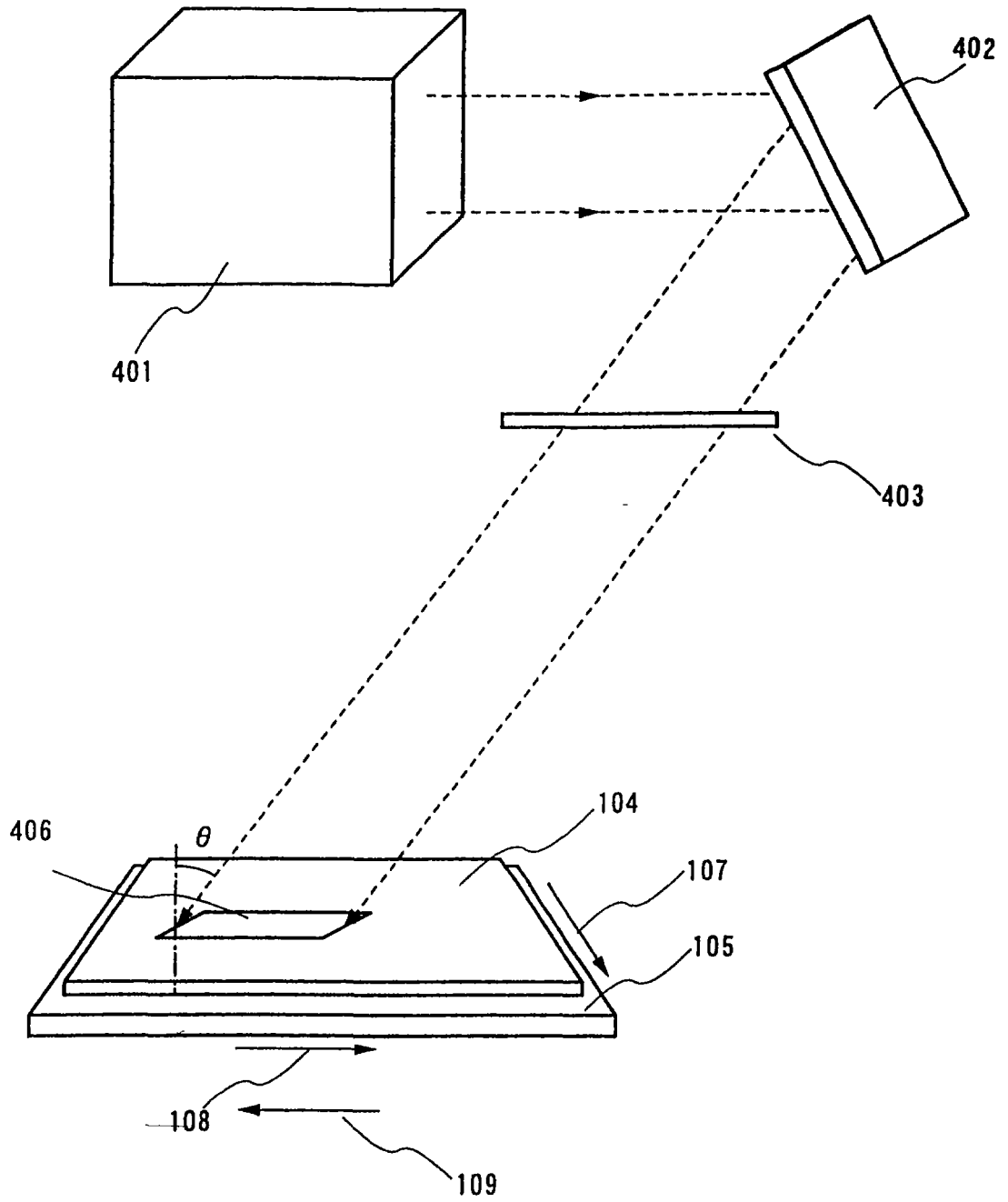
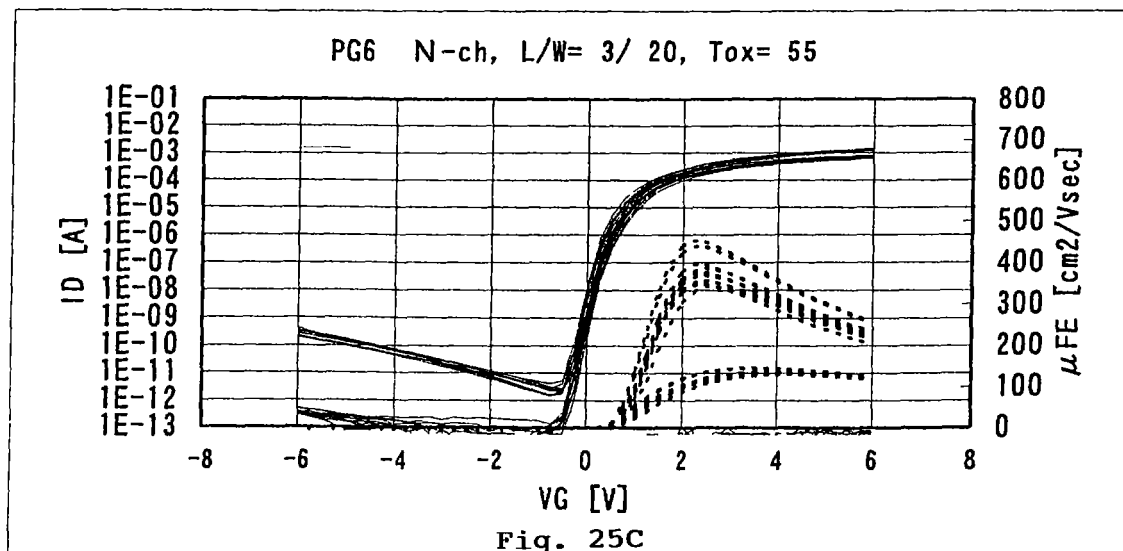
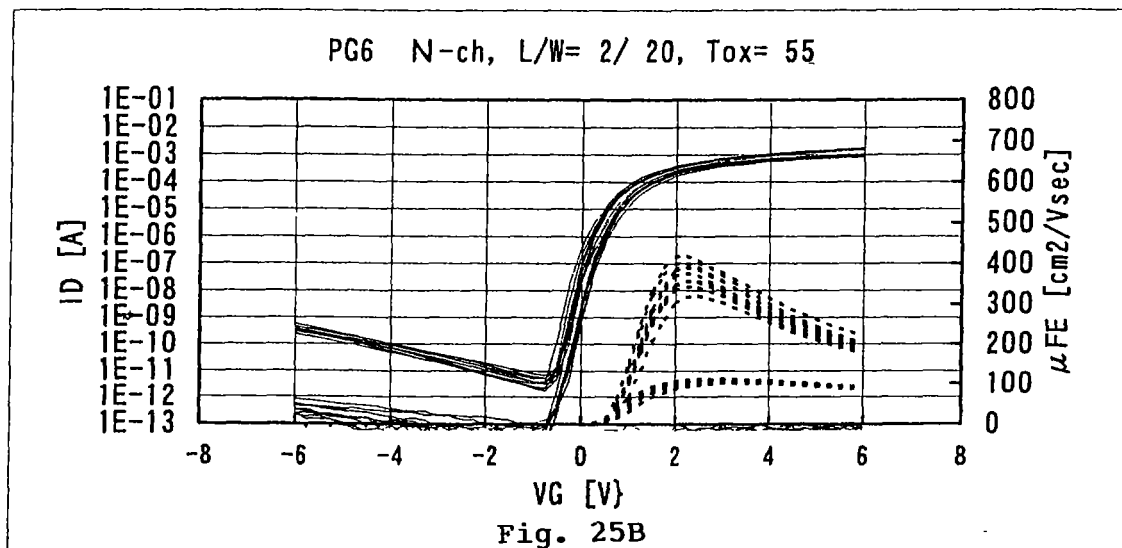
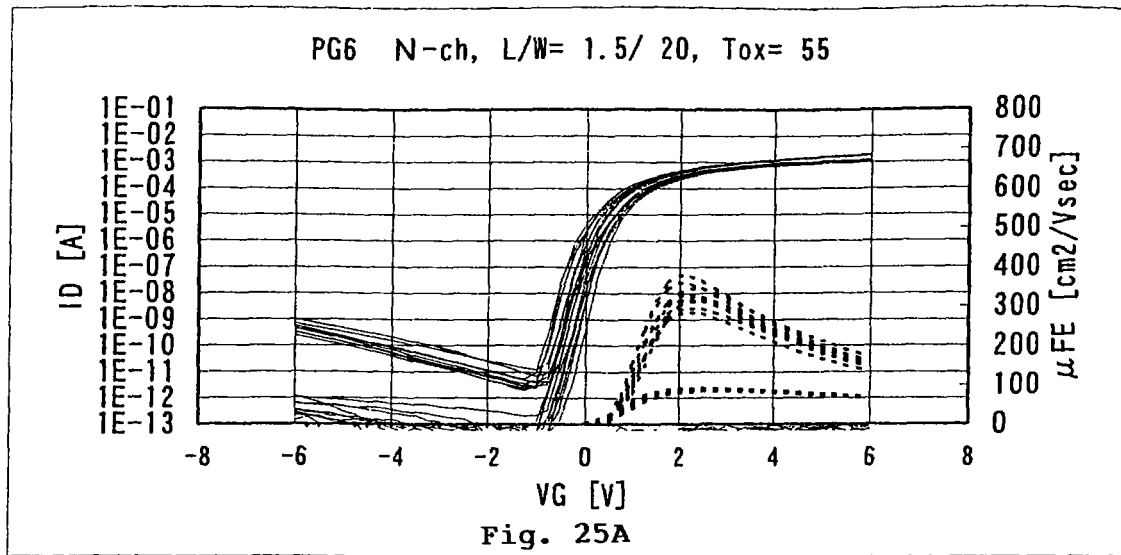


Fig. 24



LG6 N-ch, L/W= 1.5/ 20, Tox= 55

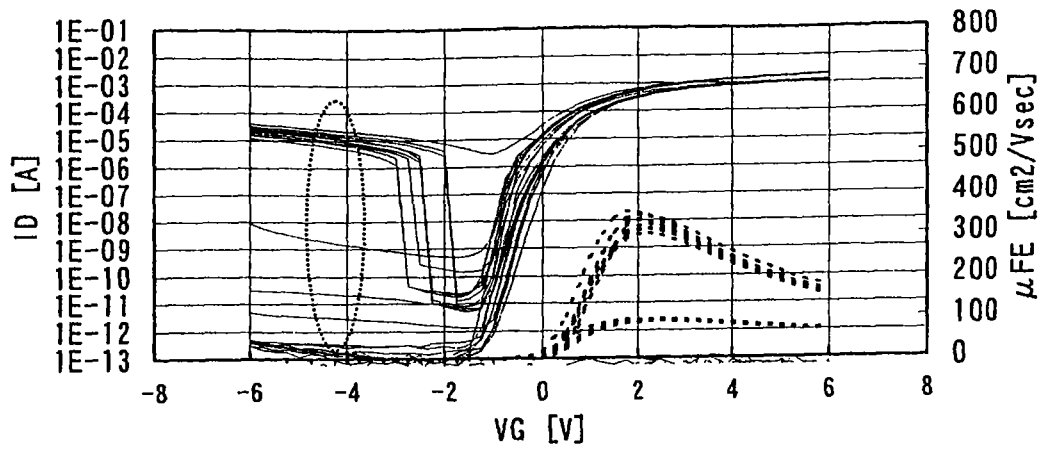


Fig.26A

LG6 N-ch, L/W= 2/ 20, Tox= 55

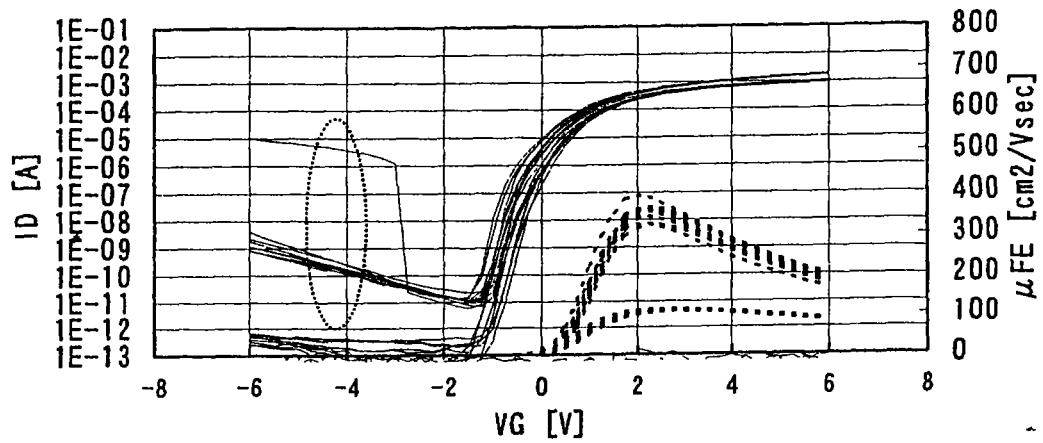


Fig. 26B

LG6 N-ch, L/W= 3/ 20, Tox= 55

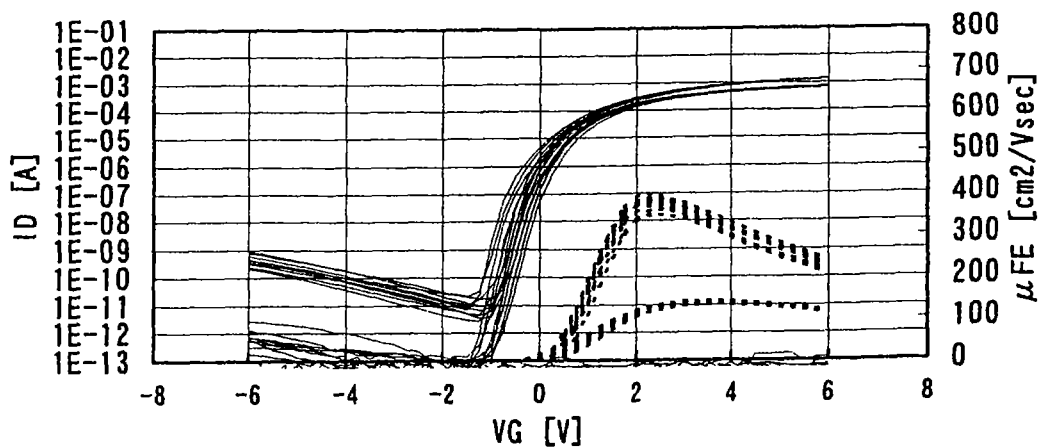


Fig.26C

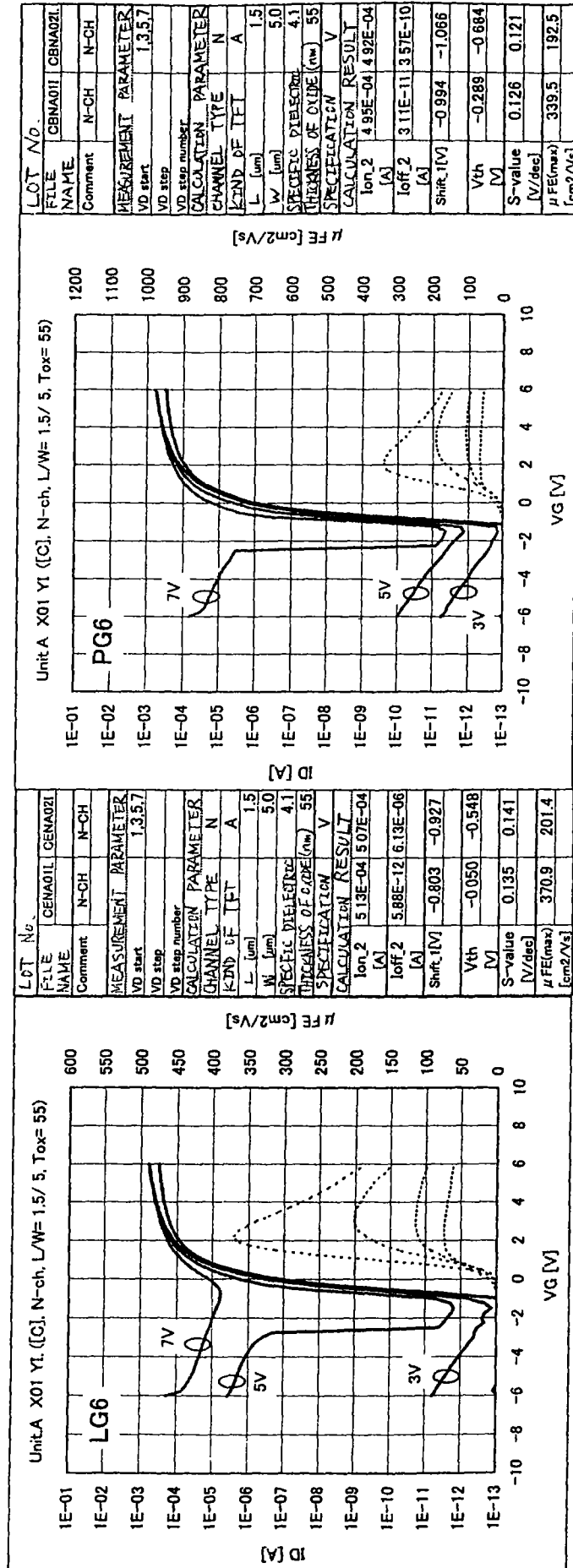
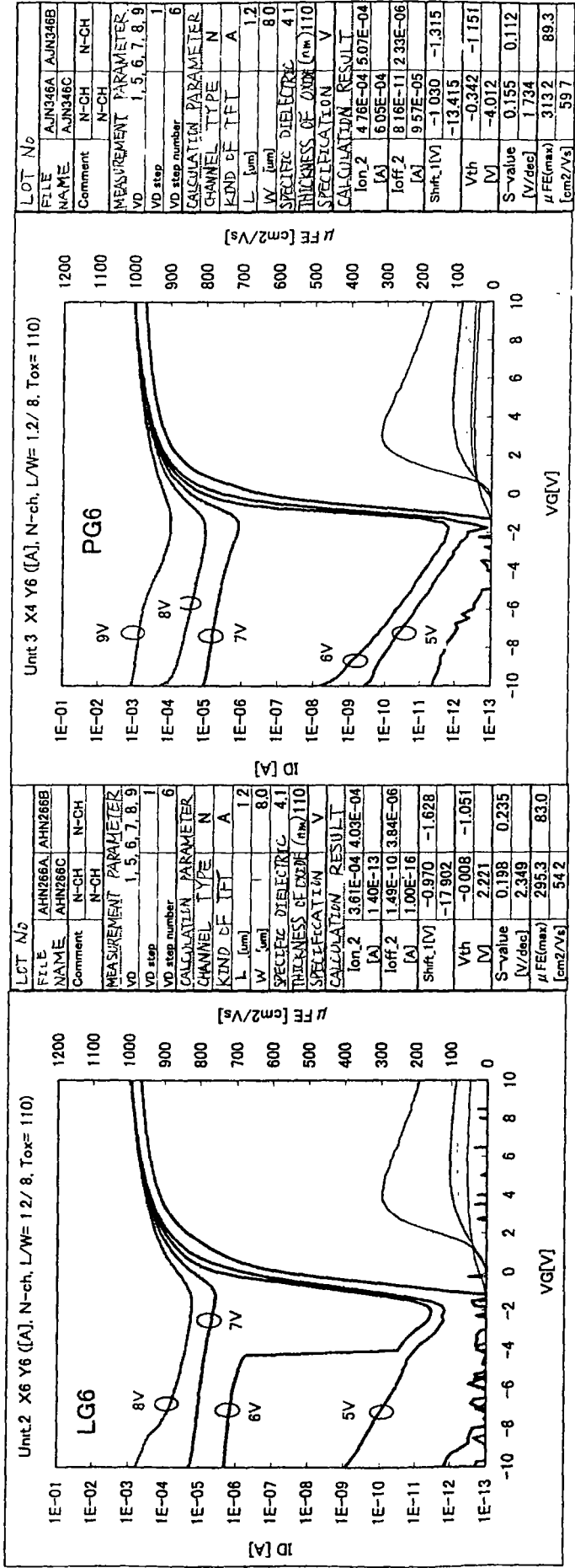


Fig.27



$L/W=1.25/8\mu m$

Fig.28 PARTIAL DEPLETION TYPE (THICKNESS OF SEMICONDUCTOR FILM IS 150nm)